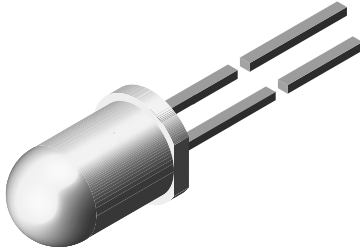


High Speed Infrared Emitting Diode, RoHS Compliant, 830 nm, GaAIAs Double Hetero



94 8389

DESCRIPTION

TSHG8400 is an infrared, 830 nm emitting diode in GaAIAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
 - Package form: T-1 $\frac{3}{4}$
 - Dimensions (in mm): \varnothing 5
 - Peak wavelength: $\lambda_p = 830$ nm
 - High reliability
 - High radiant power
 - High radiant intensity
 - Angle of half intensity: $\varphi = \pm 22^\circ$
 - Low forward voltage
 - Suitable for high pulse current operation
 - High modulation bandwidth: $f_c = 18$ MHz
 - Good spectral matching with CMOS cameras
 - Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC
- ### APPLICATIONS
- Infrared radiation source for operation with CMOS cameras (illumination)
 - High speed IR data transmission


RoHS
COMPLIANT

PRODUCT SUMMARY

| COMPONENT | I_e (mW/sr) | φ (deg) | λ_p (nm) | t_r (ns) |
|-----------|---------------|-----------------|------------------|------------|
| TSHG8400 | 70 | ± 22 | 830 | 20 |

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
|---------------|-----------|------------------------------|-------------------|
| TSHG8400 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|---------------------------------------|------------|---------------|------------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | | I_F | 100 | mA |
| Peak forward current | $t_p/T = 0.5$, $t_p = 100$ μ s | I_{FM} | 200 | mA |
| Surge forward current | $t_p = 100$ μ s | I_{FSM} | 1 | A |
| Power dissipation | | P_V | 180 | mW |
| Junction temperature | | T_j | 100 | $^\circ$ C |
| Operating temperature range | | T_{amb} | - 40 to + 85 | $^\circ$ C |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^\circ$ C |
| Soldering temperature | $t \leq 5$ s, 2 mm from case | T_{sd} | 260 | $^\circ$ C |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm soldered on PCB | R_{thJA} | 230 | K/W |

Note

$T_{amb} = 25$ $^\circ$ C, unless otherwise specified

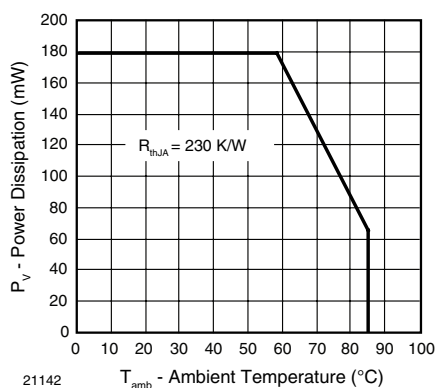


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

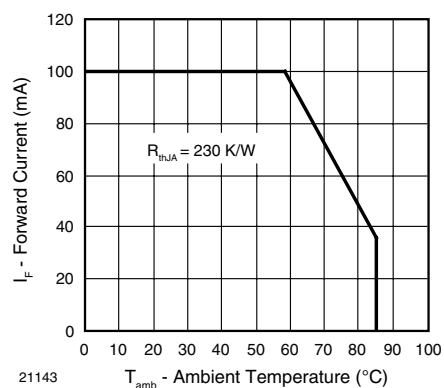


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|---|---|-----------------------------|------|--------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | I _F = 100 mA, t _p = 20 ms | V _F | | 1.5 | 1.8 | V |
| | I _F = 1 A, t _p = 100 μs | V _F | | 2.3 | | V |
| Temperature coefficient of V _F | I _F = 1 mA | TK _{V_F} | | - 1.8 | | mV/K |
| Reverse current | V _R = 5 V | I _R | | | 10 | μA |
| Junction capacitance | V _R = 0 V, f = 1 MHz, E = 0 | C _j | | 125 | | pF |
| Radiant intensity | I _F = 100 mA, t _p = 20 ms | I _e | 45 | 70 | 135 | mW/sr |
| | I _F = 1 A, t _p = 100 μs | I _e | | 700 | | mW/sr |
| Radiant power | I _F = 100 mA, t _p = 20 ms | φ _e | | 50 | | mW |
| Temperature coefficient of φ _e | I _F = 100 mA | TKφ _e | | - 0.35 | | %/K |
| Angle of half intensity | | φ | | ± 22 | | deg |
| Peak wavelength | I _F = 100 mA | λ _p | | 830 | | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 40 | | nm |
| Temperature coefficient of λ _p | I _F = 100 mA | TKλ _p | | 0.25 | | nm/K |
| Rise time | I _F = 100 mA | t _r | | 20 | | ns |
| Fall time | I _F = 100 mA | t _f | | 13 | | ns |
| Cut-off frequency | I _{DC} = 70 mA, I _{AC} = 30 mA pp | f _c | | 18 | | MHz |
| Virtual source diameter | | d | | 3.7 | | mm |

Note

T_{amb} = 25 °C, unless otherwise specified



BASIC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

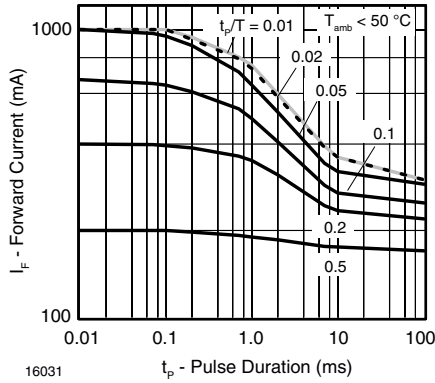


Fig. 3 - Pulse Forward Current vs. Pulse Duration

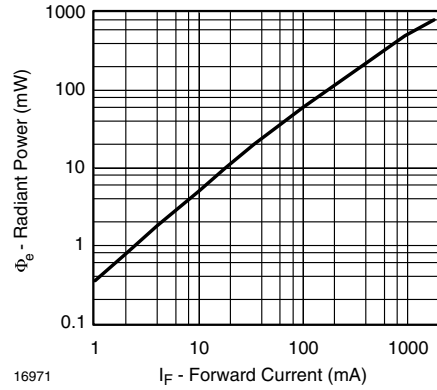


Fig. 6 - Radiant Power vs. Forward Current

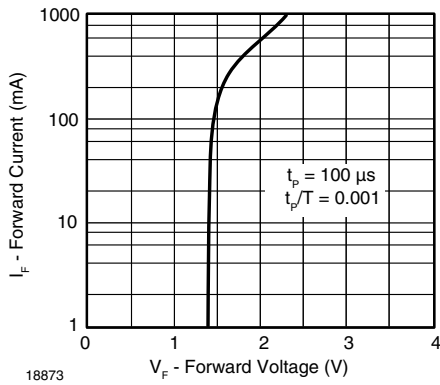


Fig. 4 - Forward Current vs. Forward Voltage

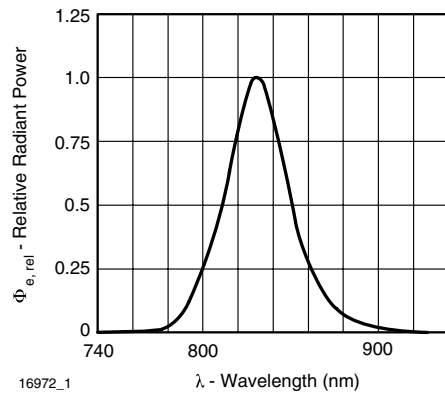


Fig. 7 - Relative Radiant Power vs. Wavelength

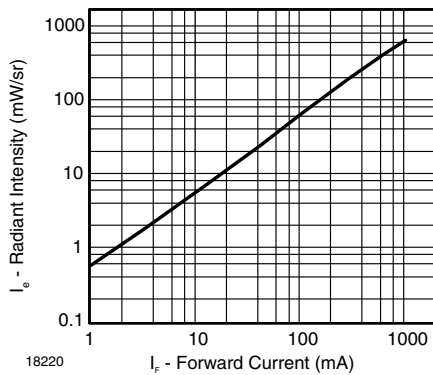


Fig. 5 - Radiant Intensity vs. Forward Current

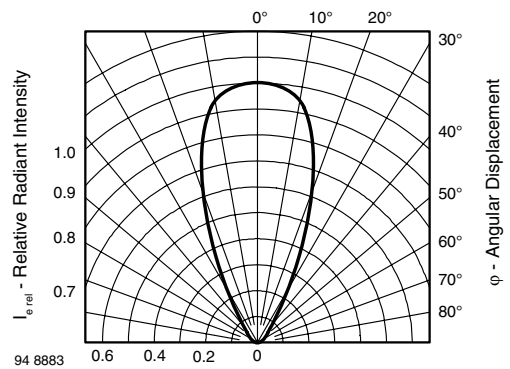


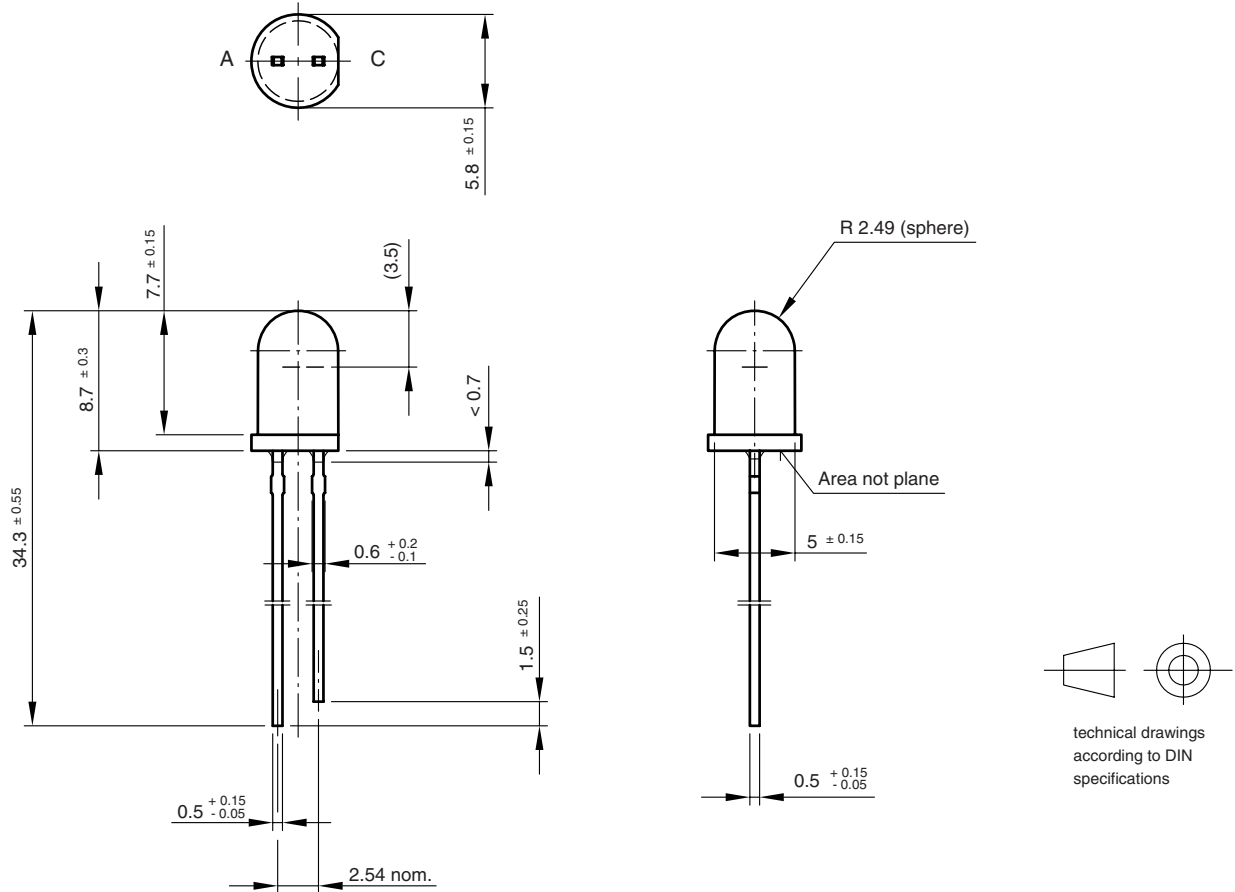
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

TSHG8400

Vishay Semiconductors High Speed Infrared Emitting Diode, RoHS Compliant, 830 nm, GaAlAs Double Hetero



PACKAGE DIMENSIONS in millimeters



6.544-5259.06-4
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19257



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